

Applications

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

Features

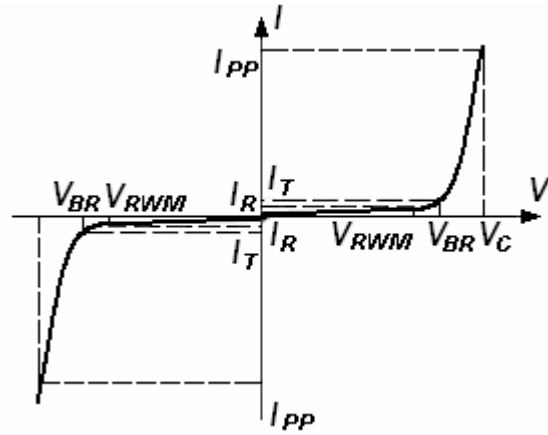
- Small Body Outline Dimensions
- 300 Watts peak pulse power ($t_p = 8/20\mu s$)
- Transient protection for data lines to
IEC 61000-4-2 (ESD) $\pm 15kV$ (air), $\pm 8kV$ (contact)
IEC 61000-4-4 (EFT) 40A (5/50ns)
IEC 61000-4-5 (Lightning) 24A (8/20 μs)
- Small package for use in portable electronics
- Suitable replacement for MLV's in ESD protection applications
- Protects one I/O or power line
- Low clamping voltage
- Working voltages: 5V and 36V
- Low leakage current
- Solid-state silicon-avalanche technology
- We declare that the material of product compliance with RoHS requirements.
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Absolute Ratings ($T_{amb}=25^{\circ}C$)

Symbol	Parameter	Value	Units	
P_{PP}	Peak Pulse Power ($t_p = 8/20 \mu s$)	300	W	
T_L	Maximum lead temperature for soldering during 10s	260	$^{\circ}C$	
T_{stg}	Storage Temperature Range	-55 to +155	$^{\circ}C$	
T_{op}	Operating Temperature Range	-40 to +125	$^{\circ}C$	
T_j	Maximum junction temperature	150	$^{\circ}C$	
	IEC61000-4-2 (ESD)	air discharge contact discharge	± 15 ± 8	KV
	IEC61000-4-4 (EFT)		40	A
	ESD Voltage	Per Human Body Model	16	KV

Electrical Parameter

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
I_T	Test Current
V_{BR}	Breakdown Voltage @ I_T



Electrical Characteristics Ratings at 25°C ambient temperature unless otherwise specified. VF = 0.9V at IF = 10mA

Device	Device Marking	V_{RWM} (V)	I_R (uA) @ V_{RWM}	V_{BR} (V) @ I_T (Note 1)	I_T	V_C (V) @ $I_{PP}=5 A^*$	V_C (V) @ Max I_{PP}^*	I_{PP} (A)*	P_{PK} (W)*	C (pF)
		Max	Max	Min	mA	Typ	Max	Max	Max	Typ
ESD3Z5V0	3M	5.0	1.0	5.6	1.0	11.6	18.6	9.4	174	35

*Surge current waveform per Figure 1.

- V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C.

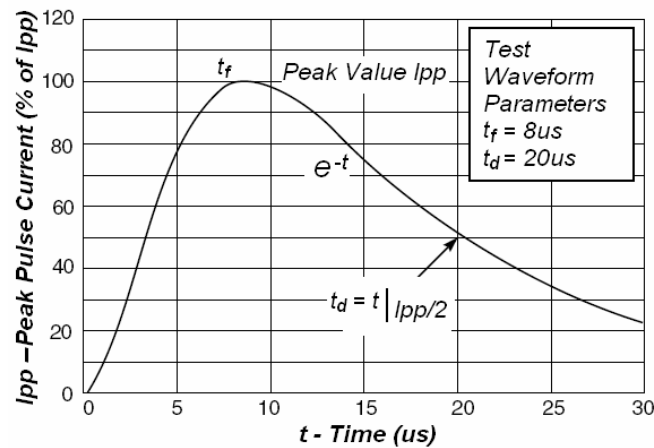


Fig1. Pulse Waveform

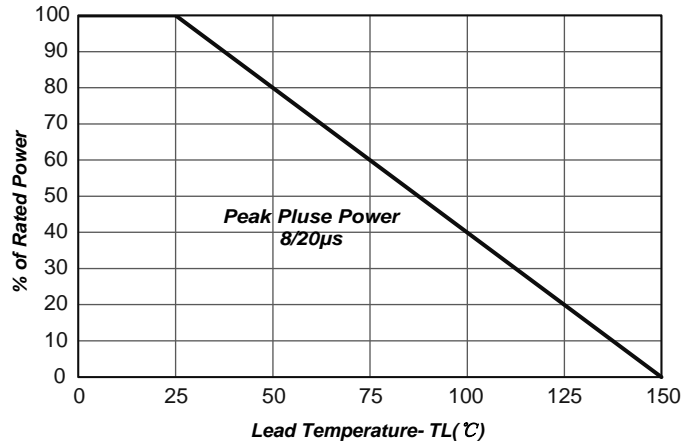
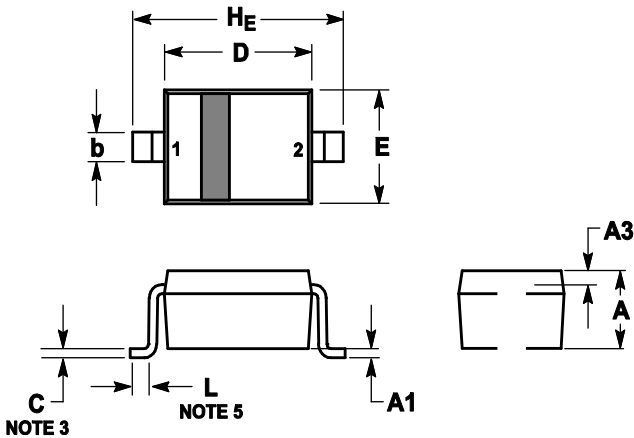


Fig2. Power Derating

SOD-323



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.8	0.9	1	0.031	0.035	0.04
A1	0	0.05	0.1	0	0.002	0.004
A3	0.15REF			0.006REF		
b	0.25	0.32	0.4	0.01	0.012	0.016
C	0.089	0.12	0.177	0.003	0.005	0.007
D	1.6	1.7	1.8	0.062	0.066	0.07
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
HE	2.3	2.5	2.7	0.09	0.098	0.105

SOLDERING FOOTPRINT

